

1. Large Signal Model Quiz

1. For a MOS transistor operating in saturation, if the aspect ratio (W/L) is doubled, then the current (I_D) is multiplied by ____.

A	8	B	2	C	4	D	1
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2. For an NMOS device, if $V_{GS} = 0.7$ V and $V_{TH} = 0.5$ V then the V_{ov} is equal to ____ V.

A	0.4	B	0.3	C	0.2	D	0.1
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3. If you have an NMOS and a PMOS, both with the same aspect ratio (W/L) and the same overdrive voltage (V_{ov}), then what is the ratio of the NMOS current to the PMOS current?

- Assume that μ_n is $450 \text{ cm}^2/\text{Vs}$ and μ_p is $150 \text{ cm}^2/\text{Vs}$.

A	2	B	1	C	4	D	3
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4. Assume an NMOS device in pinch-off saturation with $k_n = \mu_n \cdot C_{ox} \cdot W/L = 500 \text{ uA/V}^2$, $V_{TH} = 0.4$ V, the gate is connected to the ground, the drain to VDD, and the source to a current source sinking 10 uA . The voltage of the source terminal (V_S) is equal to ____ V.

A	0.6	B	-0.5	C	-0.6	D	0.5
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5. For a MOS transistor operating in pinch-off saturation, if the channel length is multiplied by 4 and I_D and W remain unchanged, then the overdrive voltage (V_{ov}) is multiplied by ____.

A	0.5	B	2	C	1	D	0.25
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6. PMOS device with body connected to VDD, if the source voltage decreases then $|V_{TH}| = ___$.

A	remains unchanged	C	The answer depends on W/L
B	Increases	D	Decreases

7. For a MOSFET operating in velocity saturation, if the overdrive voltage (V_{ov}) is doubled, then the drain current (I_D) is multiplied by ____.

A	8	B	1	C	2	D	4
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8. For a MOS transistor operating in pinch-off saturation, if the overdrive voltage (V_{ov}) is doubled, then the drain current (I_D) is multiplied by ____.

A	4	B	1	C	2	D	8
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9. For an NMOS transistor with $\mu_n = 400 \text{ cm}^2/\text{Vs}$, $L = 0.18 \text{ }\mu\text{m}$, $V_{TH} = 0.4$ V and electrons saturation velocity (V_{sat}) = 10^7 cm/s . If this MOSFET operates with $V_{GS} = 1$ V, and $V_{DS} = 1$ V, then it is operated in the ____ region.

A	Velocity Sat.	B	Triode	C	Linear	D	Pinch-off
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10. The transistor is best modeled as a ____.

A	VCVS	B	VCCS	C	CCCS	D	CCVS
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2. Small Signal Model Quiz

1. From the perspective of transconductance in analog circuits, pinch-off saturation is better than velocity saturation.

A	True	B	False
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2. Assume a MOSFET in pinch-off has a constant drain current. If the channel length is doubled and the width remains constant, then the intrinsic gain ($g_m \cdot r_o$) will be multiplied by ____.

A	0.5	B	2	C	1	D	1.4
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3. One important property that measures the performance of the transistor in analog design is the current efficiency, which is the transconductance per unit current (g_m/I_D for MOSFET). Usually we need large transconductance, but we want to spend small current because we want to save the energy of our battery. So, the higher the current efficiency, the better. The MOSFET current efficiency is equal to ____.

A	$4/V_{ov}$	B	$2/V_{ov}$	C	$1/V_{ov}$	D	$1/2 V_{ov}$
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4. Assume two MOSFETs in pinch-off saturation have the same V_{GS} and the same dimensions. They will have the same r_o regardless of V_{DS} .

A	True	B	False
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5. For a short channel MOSFET, the behavior of g_m vs V_{GS} for $V_{GS} > V_{TH}$ will be ____.

A	Quadratic then linear	C	Linear then saturates
B	Linear only	D	Quadratic only

6. One important property the measures the performance of the transistor in analog design is the intrinsic gain ($g_m \cdot r_o$). If $\lambda = 1/V_A$, then the MOSFET intrinsic gain is equal to ____.

A	$(2 \cdot V_A)/V_{ov}$	B	V_A/V_{ov}	C	$V_A/(2 \cdot V_{ov})$	D	$(4 \cdot V_A)/V_{ov}$
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7. One important property that measures the performance of the transistor in analog design is the current efficiency, which is the transconductance per unit current (g_m/I_D for MOSFET). Usually we need large transconductance, but we want to spend small current because we want to save the energy of our battery. So, the higher the current efficiency, the better. CMOS analog designers typically use an overdrive voltage of around 100-200mV. This means that if $I_D = 10 \mu A$, then g_m will be in the range of ____.

A	200-400 μS	B	10-20 μS	C	100-200 μS	D	50-100 μS
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8. For a MOSFET in pinch-off saturation being measured in the lab, if the current is quadrupled then the intrinsic gain ($g_m \cdot r_o$) will be multiplied by ____.

A	0.5	B	1	C	1.5	D	2
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9. Technology scaling improves the intrinsic gain of the transistor ($g_m \cdot r_o$).

A	True	B	False
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10. Assume a MOSFET in pinch-off has a constant drain current. If the overdrive voltage is doubled, then g_m will be multiplied by ____.

A	0.25	B	0.5	C	2	D	1
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